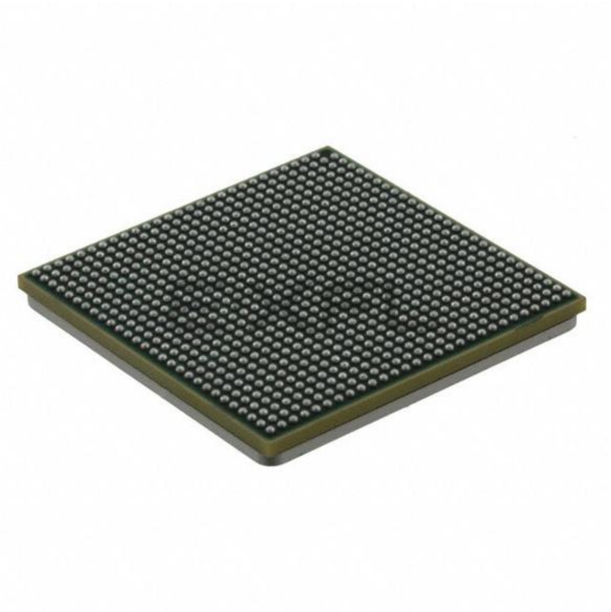

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8548epxaqgd

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the device. This device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings [1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.21	V	—
PLL supply voltage		AV_{DD}	–0.3 to 1.21	V	—
Core power supply for SerDes transceivers		SV_{DD}	–0.3 to 1.21	V	—
Pad power supply for SerDes transceivers		XV_{DD}	–0.3 to 1.21	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	2
Three-speed Ethernet I/O voltage		LV_{DD} (for eTSEC1 and eTSEC2) TV_{DD} (for eTSEC3 and eTSEC4)	–0.3 to 3.63 –0.3 to 2.75 –0.3 to 3.63 –0.3 to 2.75	V	3
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Local bus I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75	V	—
Input voltage	DDR/DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	4
	DDR/DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD}/2 + 0.3)	V	—
	Three-speed Ethernet I/O signals	LV_{IN} TV_{IN}	–0.3 to (LV_{DD} + 0.3) –0.3 to (TV_{DD} + 0.3)	V	4
	Local bus signals	BV_{IN}	–0.3 to (BV_{DD} + 0.3)	—	—
	DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4
	PCI/PCI-X	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	4

Table 1. Absolute Maximum Ratings [1] (continued)

Characteristic	Symbol	Max Value	Unit	Notes
Storage temperature range	T_{STG}	–55 to 150	°C	—

Notes:

1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. The –0.3 to 2.75 V range is for DDR and –0.3 to 1.98 V range is for DDR2.
3. The 3.63 V maximum is only supported when the port is configured in GMII, MII, RMII, or TBI modes; otherwise the 2.75 V maximum applies. See Section 8.2, “FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications,” for details on the recommended operating conditions per protocol.
4. (M,L,O)V_{IN} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

The following table provides the recommended operating conditions for this device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic		Symbol	Recommended Value	Unit	Notes
Core supply voltage		V_{DD}	1.1 V ± 55 mV	V	—
PLL supply voltage		AV_{DD}	1.1 V ± 55 mV	V	1
Core power supply for SerDes transceivers		SV_{DD}	1.1 V ± 55 mV	V	—
Pad power supply for SerDes transceivers		XV_{DD}	1.1 V ± 55 mV	V	—
DDR and DDR2 DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O voltage		LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	4
		TV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	—	4
PCI/PCI-X, DUART, system control and power management, I^2C, Ethernet MII management, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	3
Local bus I/O voltage		BV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V	—
Input voltage	DDR and DDR2 DRAM signals	MV_{IN}	GND to GV_{DD}	V	2
	DDR and DDR2 DRAM reference	MV_{REF}	GND to $GV_{DD}/2$	V	2
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	GND to LV_{DD} GND to TV_{DD}	V	4
	Local bus signals	BV_{IN}	GND to BV_{DD}	V	—
	PCI, DUART, SYSCLK, system control and power management, I^2C, Ethernet MII management, and JTAG signals	OV_{IN}	GND to OV_{DD}	V	3

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that GV_{DD}(typ) = 2.5 V for DDR SDRAM, and GV_{DD}(typ) = 1.8 V for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when GV_{DD}(typ) = 1.8 V.

Table 11. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} – 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} – 0.125$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \le V_{OUT} \le GV_{DD}$.

This table provides the DDR2 I/O capacitance when GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.15$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.15$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

Figure 4 shows the DDR SDRAM output timing diagram.+

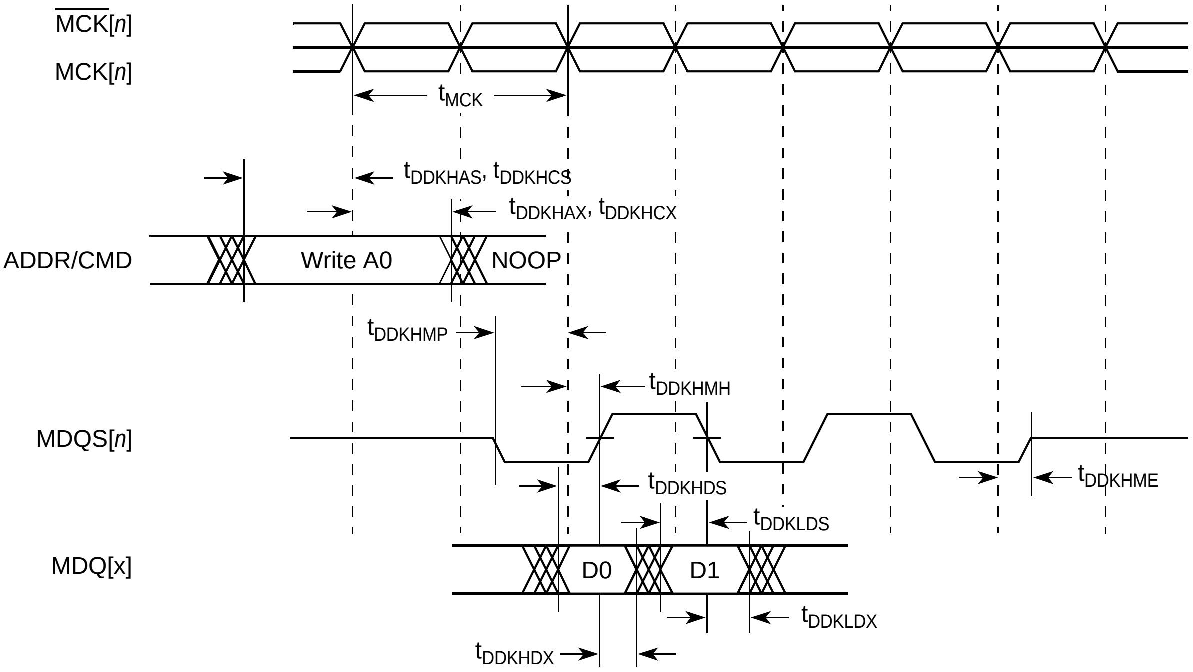

Figure 4. DDR SDRAM Output Timing Diagram

Figure 5 provides the AC test load for the DDR bus.

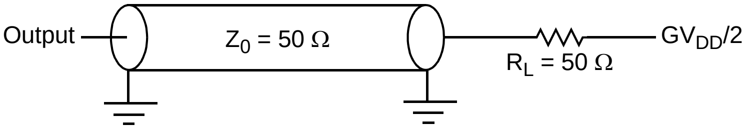

Figure 5. DDR AC Test Load

Figure 19 provides the AC test load for eTSEC.

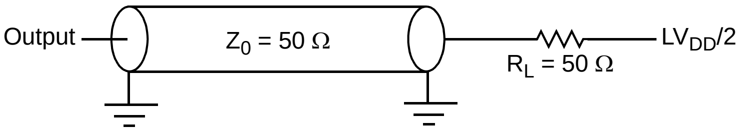

Figure 19. eTSEC AC Test Load

Figure 20 shows the RMII receive AC timing diagram.

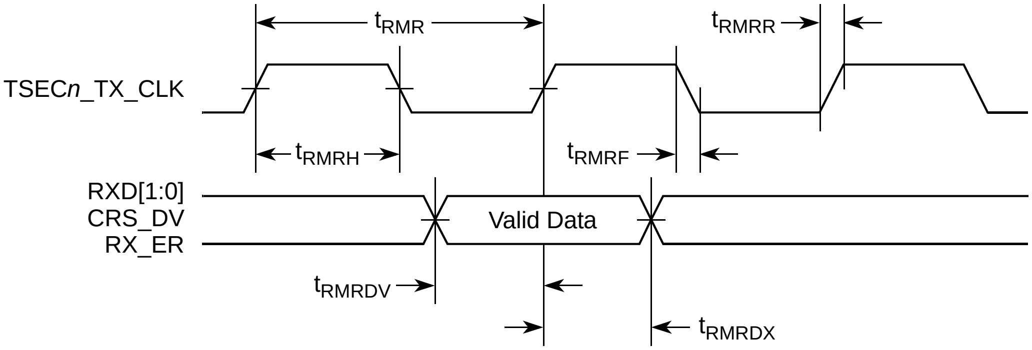

Figure 20. RMII Receive AC Timing Diagram

Table 53. PCI-X AC Timing Specifications at 66 MHz (continued)

Parameter	Symbol	Min	Max	Unit	Notes
$\overline{\text{HRESET}}$ to PCI-X initialization pattern hold time	t_{PCRHIX}	0	50	ns	6, 11

Notes:

1. See the timing measurement conditions in the *PCI-X 1.0a Specification*.
2. Minimum times are measured at the package pin (not the test point). Maximum times are measured with the test point and load circuit.
3. Setup time for point-to-point signals applies to $\overline{\text{REQ}}$ and $\overline{\text{GNT}}$ only. All other signals are bused.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Setup time applies only when the device is not driving the pin. Devices cannot drive and receive signals at the same time.
6. Maximum value is also limited by delay to the first transaction (time for $\overline{\text{HRESET}}$ high to first configuration access, t_{PCRHFV}). The PCI-X initialization pattern control signals after the rising edge of $\overline{\text{HRESET}}$ must be negated no later than two clocks before the first $\overline{\text{FRAME}}$ and must be floated no later than one clock before $\overline{\text{FRAME}}$ is asserted.
7. A PCI-X device is permitted to have the minimum values shown for t_{PCKHOV} and t_{CYC} only in PCI-X mode. In conventional mode, the device must meet the requirements specified in PCI 2.2 for the appropriate clock frequency.
8. Device must meet this specification independent of how many outputs switch simultaneously.
9. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI-X 1.0a Specification.*
10. Guaranteed by characterization.
11. Guaranteed by design.

This table provides the PCI-X AC timing specifications at 133 MHz. Note that the maximum PCI-X frequency in synchronous mode is 110 MHz.

Table 54. PCI-X AC Timing Specifications at 133 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	t_{PCKHOV}	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t_{PCKHOX}	0.7	—	ns	1, 11
SYSCLK to output high impedance	t_{PCKHOZ}	—	7	ns	1, 4, 8, 12
Input setup time to SYSCLK	t_{PCIVKH}	1.2	—	ns	3, 5, 9, 11
Input hold time from SYSCLK	t_{PCIXKH}	0.5	—	ns	11
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ setup time	t_{PCRVRH}	10	—	clocks	12
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	12
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	10, 12
PCI-X initialization pattern to $\overline{\text{HRESET}}$ setup time	t_{PCIVRH}	10	—	clocks	12

Table 54. PCI-X AC Timing Specifications at 133 MHz (continued)

Parameter	Symbol	Min	Max	Unit	Notes
$\overline{\text{HRESET}}$ to PCI-X initialization pattern hold time	t_{PCRHIX}	0	50	ns	6, 12

Notes:

1. See the timing measurement conditions in the *PCI-X 1.0a Specification*.
2. Minimum times are measured at the package pin (not the test point). Maximum times are measured with the test point and load circuit.
3. Setup time for point-to-point signals applies to $\overline{\text{REQ}}$ and $\overline{\text{GNT}}$ only. All other signals are bused.
4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
5. Setup time applies only when the device is not driving the pin. Devices cannot drive and receive signals at the same time.
6. Maximum value is also limited by delay to the first transaction (time for $\overline{\text{HRESET}}$ high to first configuration access, t_{PCRHFV}). The PCI-X initialization pattern control signals after the rising edge of HRESET must be negated no later than two clocks before the first $\overline{\text{FRAME}}$ and must be floated no later than one clock before $\overline{\text{FRAME}}$ is asserted.
7. A PCI-X device is permitted to have the minimum values shown for t_{PCKHOV} and t_{CYC} only in PCI-X mode. In conventional mode, the device must meet the requirements specified in PCI 2.2 for the appropriate clock frequency.
8. Device must meet this specification independent of how many outputs switch simultaneously.
9. The timing parameter t_{PCIVKH} is a minimum of 1.4 ns rather than the minimum of 1.2 ns in the *PCI-X 1.0a Specification.*
10. The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI-X 1.0a Specification.*
11. Guaranteed by characterization.
12. Guaranteed by design.

17 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the MPC8548E.

17.1 DC Requirements for PCI Express SD_REF_CLK and SD_REF_CLK

For more information, see Section 16.2, "SerDes Reference Clocks."

17.2 AC Requirements for PCI Express SerDes Clocks

Table 55 lists the AC requirements for the PCI Express SerDes clocks.

Table 55. SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typ	Max	Unit	Notes
t_{REF}	REFCLK cycle time	—	10	—	ns	1
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles.	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location.	–50	—	50	ps	—

Note:

1. Typical based on *PCI Express Specification 2.0*.

17.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million (ppm) of each other at all times. This is specified to allow bit rate clock sources with a ±300 ppm tolerance.

17.4 Physical Layer Specifications

The following is a summary of the specifications for the physical layer of PCI Express on this device. For further details as well as the specifications of the transport and data link layer see *PCI Express Base Specification. Rev. 1.0a*.

17.4.1 Differential Transmitter (TX) Output

Table 56 defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

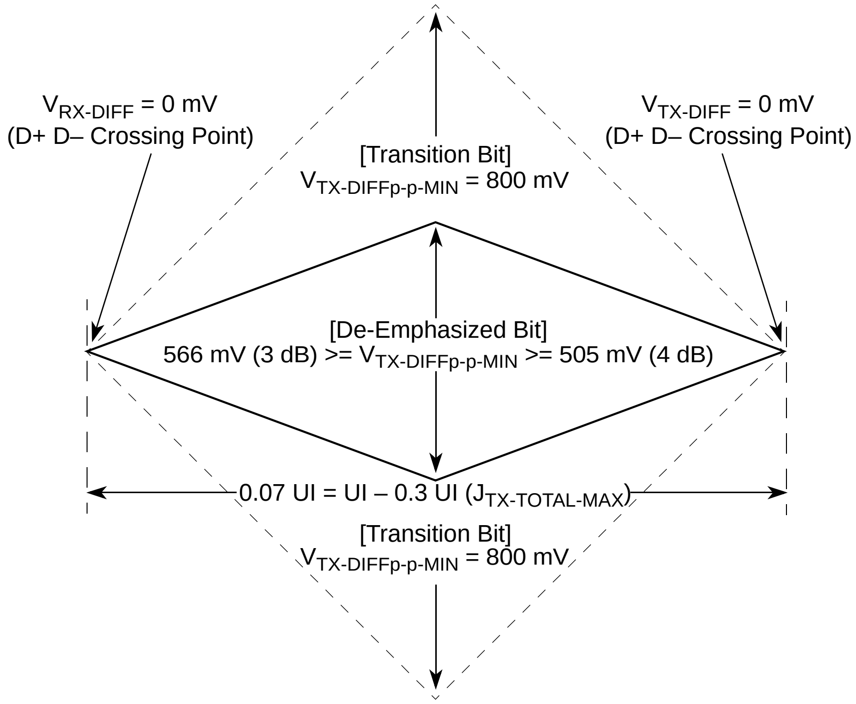

Figure 48. Minimum Transmitter Timing and Voltage Output Compliance Specifications

17.4.3 Differential Receiver (RX) Input Specifications

Table 57 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Table 57. Differential Receiver (RX) Input Specifications

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
$V_{RX-DIFFp-p}$	Differential peak-to-peak input voltage	0.175	—	1.200	V	$V_{RX-DIFFp-p} = 2 \times \|V_{RX-D+} - V_{RX-D-}\|$. See Note 2.
T_{RX-EYE}	Minimum receiver eye width	0.4	—	—	UI	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6$ UI. See Notes 2 and 3.
$T_{RX-EYE-MEDIAN-to-MAX-JITTER}$	Maximum time between the jitter median and maximum deviation from the median	—	—	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3, and 7.

19.3 Pinout Listings

NOTE

The DMA_DACK[0:1] and TEST_SEL/TEST_SEL pins must be set to a proper state during POR configuration. See the pinlist table of the individual device for more details.

For MPC8548/47/45, GPIOs are still available on PCI1_AD[63:32]/PC2_AD[31:0] pins if they are not used for PCI functionality.

For MPC8545/43, eTSEC does not support 16 bit FIFO mode.

Table 71 provides the pinout listing for the MPC8548E 783 FC-PBGA package.

Table 71. MPC8548E Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1 and PCI2 (One 64-Bit or Two 32-Bit)				
PCI1_AD[63:32]/PCI2_AD[31:0]	AB14, AC15, AA15, Y16, W16, AB16, AC16, AA16, AE17, AA18, W18, AC17, AD16, AE16, Y17, AC18, AB18, AA19, AB19, AB21, AA20, AC20, AB20, AB22, AC22, AD21, AB23, AF23, AD23, AE23, AC23, AC24	I/O	OV_{DD}	17
PCI1_AD[31:0]	AH6, AE7, AF7, AG7, AH7, AF8, AH8, AE9, AH9, AC10, AB10, AD10, AG10, AA10, AH10, AA11, AB12, AE12, AG12, AH12, AB13, AA12, AC13, AE13, Y14, W13, AG13, V14, AH13, AC14, Y15, AB15	I/O	OV_{DD}	17
PCI1_C_BE[7:4]/PCI2_C_BE[3:0]	AF15, AD14, AE15, AD15	I/O	OV_{DD}	17
PCI1_C_BE[3:0]	AF9, AD11, Y12, Y13	I/O	OV_{DD}	17
PCI1_PAR64/PCI2_PAR	W15	I/O	OV_{DD}	
PCI1_GNT[4:1]	AG6, AE6, AF5, AH5	O	OV_{DD}	5, 9, 35
PCI1_GNT0	AG5	I/O	OV_{DD}	—
PCI1_IRDY	AF11	I/O	OV_{DD}	2
PCI1_PAR	AD12	I/O	OV_{DD}	—
PCI1_PERR	AC12	I/O	OV_{DD}	2
PCI1_SERR	V13	I/O	OV_{DD}	2, 4
PCI1_STOP	W12	I/O	OV_{DD}	2
PCI1_TRDY	AG11	I/O	OV_{DD}	2

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LSYNC_IN	F27	I	BV_{DD}	—
LSYNC_OUT	F28	O	BV_{DD}	—
DMA				
$\overline{\text{DMA\_DACK}}$[0:1]	AD3, AE1	O	OV_{DD}	5, 9, 102
$\overline{\text{DMA\_DREQ}}$[0:1]	AD4, AE2	I	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	AD2, AD1	O	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{UDE}}$	AH16	I	OV_{DD}	—
$\overline{\text{MCP}}$	AG19	I	OV_{DD}	—
IRQ[0:7]	AG23, AF18, AE18, AF20, AG18, AF17, AH24, AE20	I	OV_{DD}	—
IRQ[8]	AF19	I	OV_{DD}	—
IRQ[9]/$\overline{\text{DMA\_DREQ3}}$	AF21	I	OV_{DD}	1
IRQ[10]/$\overline{\text{DMA\_DACK3}}$	AE19	I/O	OV_{DD}	1
IRQ[11]/$\overline{\text{DMA\_DDONE3}}$	AD20	I/O	OV_{DD}	1
$\overline{\text{IRQ\_OUT}}$	AD18	O	OV_{DD}	2, 4
Ethernet Management Interface				
EC_MDC	AB9	O	OV_{DD}	5, 9
EC_MDIO	AC8	I/O	OV_{DD}	—
Gigabit Reference Clock				
EC_GTX_CLK125	V11	I	LV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_RXD[7:0]	R5, U1, R3, U2, V3, V1, T3, T2	I	LV_{DD}	—
TSEC1_TXD[7:0]	T10, V7, U10, U5, U4, V6, T5, T8	O	LV_{DD}	5, 9
TSEC1_COL	R4	I	LV_{DD}	—
TSEC1_CRS	V5	I/O	LV_{DD}	20
TSEC1_GTX_CLK	U7	O	LV_{DD}	—
TSEC1_RX_CLK	U3	I	LV_{DD}	—
TSEC1_RX_DV	V2	I	LV_{DD}	—
TSEC1_RX_ER	T1	I	LV_{DD}	—
TSEC1_TX_CLK	T6	I	LV_{DD}	—
TSEC1_TX_EN	U9	O	LV_{DD}	30
TSEC1_TX_ER	T7	O	LV_{DD}	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Clock				
RTC	AF16	I	OV_{DD}	—
SYSCLK	AH17	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	12
TDO	AF28	O	OV_{DD}	—
TMS	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV_{DD}	12
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV_{DD}	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
FIFO1_RXC2	P5	I	LV$_{DD}$	104
Reserved	R1	—	—	104
Reserved	P10	—	—	105
FIFO1_TXC2	P7	O	LV$_{DD}$	15
cfg_dram_type1	R10	I	LV$_{DD}$	5
Three-Speed Ethernet Controller (Gigabit Ethernet 3)				
TSEC3_TXD[3:0]	V8, W10, Y10, W7	O	TV$_{DD}$	5, 9, 29
TSEC3_RXD[3:0]	Y1, W3, W5, W4	I	TV$_{DD}$	—
TSEC3_GTX_CLK	W8	O	TV$_{DD}$	—
TSEC3_RX_CLK	W2	I	TV$_{DD}$	—
TSEC3_RX_DV	W1	I	TV$_{DD}$	—
TSEC3_RX_ER	Y2	I	TV$_{DD}$	—
TSEC3_TX_CLK	V10	I	TV$_{DD}$	—
TSEC3_TX_EN	V9	O	TV$_{DD}$	30
TSEC3_TXD[7:4]	AB8, Y7, AA7, Y8	O	TV$_{DD}$	5, 9, 29
TSEC3_RXD[7:4]	AA1, Y3, AA2, AA4	I	TV$_{DD}$	—
Reserved	AA5	—	—	15
TSEC3_COL	Y5	I	TV$_{DD}$	—
TSEC3_CRS	AA3	I/O	TV$_{DD}$	31
TSEC3_TX_ER	AB6	O	TV$_{DD}$	—
DUART				
$\overline{\text{UART\_CTS}}$[0:1]	AB3, AC5	I	OV$_{DD}$	—
$\overline{\text{UART\_RTS}}$[0:1]	AC6, AD7	O	OV$_{DD}$	—
UART_SIN[0:1]	AB5, AC7	I	OV$_{DD}$	—
UART_SOUT[0:1]	AB7, AD8	O	OV$_{DD}$	—
I^{2}C interface				
IIC1_SCL	AG22	I/O	OV$_{DD}$	4, 27
IIC1_SDA	AG21	I/O	OV$_{DD}$	4, 27
IIC2_SCL	AG15	I/O	OV$_{DD}$	4, 27
IIC2_SDA	AG14	I/O	OV$_{DD}$	4, 27
SerDes				
SD_RX[0:3]	M28, N26, P28, R26	I	XV$_{DD}$	—
$\overline{\text{SD\_RX}}$[0:3]	M27, N25, P27, R25	I	XV$_{DD}$	—
SD_TX[0:3]	M22, N20, P22, R20	O	XV$_{DD}$	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—
SD_IMP_CAL_RX	L28	I	200 Ω (±1%) to GND	—
SD_IMP_CAL_TX	AB26	I	100 Ω (±1%) to GND	—
SD_PLL_TPA	U26	O	AVDD_SRDS	24

Note: All note references in this table use the same numbers as those for Table 71. See Table 71 for the meanings of these notes.

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	$R_{\theta JB}$	3	°C/W	3
Die junction-to-case	N/A	$R_{\theta JC}$	0.8	°C/W	4

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package Thermal Characteristics for FC-PBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	9	°C/W	1, 2

- $\overline{\text{SD\_REF\_CLK}}$

NOTE

> It is recommended to power down the unused lane through SRDSCR1[0:7] register (offset = 0xE_0F08) (this prevents the oscillations and holds the receiver output in a fixed state) that maps to SERDES lane 0 to lane 7 accordingly.

Pins V28 and M26 must be tied to XV_{DD}. Pins V27 and M25 must be tied to GND through a 300-Ω resistor.

22.11 Guideline for PCI Interface Termination

PCI termination if PCI 1 or PCI 2 is not used at all.

Option 1

If PCI arbiter is enabled during POR:

- All AD pins are driven to the stable states after POR. Therefore, all ADs pins can be floating.
- All PCI control pins can be grouped together and tied to OV_{DD} through a single 10-kΩ resistor.
- It is optional to disable PCI block through DEVDISR register after POR reset.

Option 2

If PCI arbiter is disabled during POR:

- All AD pins are in the input state. Therefore, all ADs pins need to be grouped together and tied to OV_{DD} through a single (or multiple) 10-kΩ resistor(s).
- All PCI control pins can be grouped together and tied to OV_{DD} through a single 10-kΩ resistor.
- It is optional to disable PCI block through DEVDISR register after POR reset.

22.12 Guideline for LBIU Termination

If the LBIU parity pins are not used, the following is the termination recommendation:

- For LDP[0:3]—tie them to ground or the power supply rail via a 4.7-kΩ resistor.
- For LPBSE—tie it to the power supply rail via a 4.7-kΩ resistor (pull-up resistor).

Table 87. Part Numbering Nomenclature (continued)

MPC	*nnnnn*	*t*	*pp*	*ff*	*c*	*r*
Product Code	**Part Identifier**	**Temperature**	**Package[1, 2, 3]**	**Processor Frequency[4]**	**Core Frequency**	**Silicon Version**
MPC	8545E	Blank = 0 to 105°C C = –40° to 105°C	HX = CBGA VU = Pb-free CBGA PX = PBGA VT = Pb-free PBGA	AT = 1200 AQ = 1000 AN = 800	G = 400	Blank = Ver. 2.0 (SVR = 0x80390220) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x80390231)
	8545					Blank = Ver. 2.0 (SVR = 0x80310220) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x80310231)
	8543E			AQ = 1000 AN = 800		Blank = Ver. 2.0 (SVR = 0x803A0020) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x803A0031)
	8543					Blank = Ver. 2.0 (SVR = 0x80320020) A = Ver. 2.1.1 B = Ver. 2.1.2 D = Ver. 3.1.x (SVR = 0x80320031)

Notes:

1. See Section 19, “Package Description,” for more information on available package types.
2. The HiCTE FC-CBGA package is available on only Version 2.0 of the device.
3. The FC-PBGA package is available on only Version 2.1.1, 2.1.2, and 2.1.3 of the device.
4. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by part number specifications may support other maximum core frequencies.
5. This speed available only for silicon Version 2.1.1, 2.1.2, and 2.1.3.